

semiconductor film with a gate insulating film interposed therebetween.

44. (New) A method according to claim 41, further comprising a step of forming gate electrode over said substrate before forming said semiconductor film.

45. (New) A method according to claim 41, wherein said semiconductor device having an EL display device.

REMARKS

Reconsideration and allowance of the above-referenced application are respectfully requested. The foregoing amendments are responsive to the October 24, 2000 Office Action. Applicant respectfully requests entry of the requested amendments and reconsideration of the application in view of the following comments.

Response to the Claim Rejections Under 35 U.S.C. § 102

Claim 1 is rejected under 35 U.S.C. § 102(e) as being anticipated by U.S. Patent No. 5,712,191 issued to Nakajima, et

Applicant respectfully requests allowance of dependent Claims 3-7, 9-13, 15-19, 21-28, 30-35, 37-40, and 42-45.

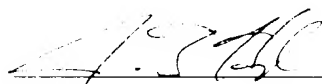
Summary

In view of the above amendments and remarks, all of the claims should be in condition for allowance. A formal notice to that effect is respectfully solicited.

Please apply any charges or credits to Deposit Account No. 06-1050.

Respectfully submitted,

Date: 1/24/01


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